# NLSV2T244

# 2-Bit Dual-Supply Non-Inverting Level Translator

The NLSV2T244 is a 2-bit configurable dual-supply voltage level translator. The input  $A_n$  and output  $B_n$  ports are designed to track two different power supply rails,  $V_{CCA}$  and  $V_{CCB}$  respectively. Both supply rails are configurable from 0.9 V to 4.5 V allowing universal low-voltage translation from the input  $A_n$  to the output  $B_n$  port.

#### Features

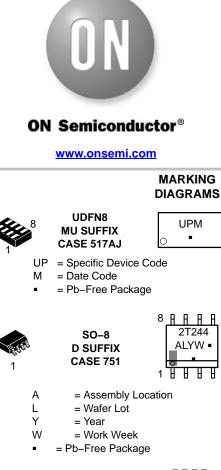
- Wide V<sub>CCA</sub> and V<sub>CCB</sub> Operating Range: 0.9 V to 4.5 V
- High-Speed w/ Balanced Propagation Delay
- Inputs and Outputs have OVT Protection to 4.5 V
- Non-preferential V<sub>CCA</sub> and V<sub>CCB</sub> Sequencing
- Outputs at 3–State until Active V<sub>CC</sub> is Reached
- Power–Off Protection
- Outputs Switch to 3-State with V<sub>CCB</sub> at GND
- Small Packaging: UDFN8, SO-8, Micro8
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

#### **Typical Applications**

• Mobile Phones, PDAs, Other Portable Devices

#### Important Information

• ESD Protection for All Pins: HBM (Human Body Model) > 5000 V





A



= Assembly Location

Micro8

**DM SUFFIX** 

CASE 846A

- = Year
- W = Work Week
- = Pb–Free Package

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
NLSV2T244MUTAG	UDFN8 (Pb–Free)	3000 / Tape & Reel
NLSV2T244DR2G	SO-8 (Pb-Free)	2500 / Tape & Reel
NLSV2T244DMR2G	Micro8 (Pb-Free)	4000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

# NLSV2T244

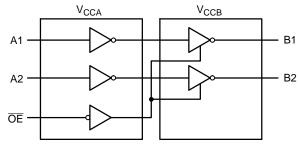
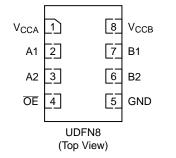
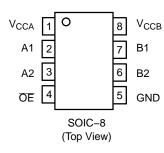
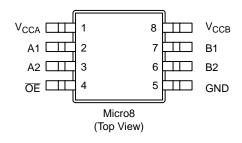


Figure 1. Logic Diagram

## **PIN ASSIGNMENTS**







### **PIN ASSIGNMENT**

PIN	FUNCTION
V <sub>CCA</sub>	Input Port DC Power Supply
V <sub>CCB</sub>	Output Port DC Power Supply
GND	Ground
A <sub>n</sub>	Input Port
B <sub>n</sub>	Output Port
ŌĒ	Output Enable

## **TRUTH TABLE**

In	Outputs	
ŌĒ	A <sub>n</sub>	B <sub>n</sub>
L	L	L
L	Н	Н
Н	х	3-State

## MAXIMUM RATINGS

Symbol	Rating		Value	Condition	Unit
$V_{CCA}, V_{CCB}$	DC Supply Voltage		-0.5 to +5.5		V
VI	DC Input Voltage	A <sub>n</sub>	-0.5 to +5.5		V
V <sub>C</sub>	Control Input	OE	-0.5 to +5.5		V
V <sub>O</sub>	DC Output Voltage (Power Down)	B <sub>n</sub>	-0.5 to +5.5	$V_{CCA} = V_{CCB} = 0$	V
	(Active Mode)	Bn	-0.5 to +5.5		V
	(Tri-State Mode)	Bn	-0.5 to +5.5		V
I <sub>IK</sub>	DC Input Diode Current		-20	V <sub>I</sub> < GND	mA
I <sub>OK</sub>	DC Output Diode Current		-50	V <sub>O</sub> < GND	mA
Ι <sub>Ο</sub>	DC Output Source/Sink Current		±50		mA
I <sub>CCA</sub> , I <sub>CCB</sub>	DC Supply Current Per Supply Pin		±100		mA
I <sub>GND</sub>	DC Ground Current per Ground Pin		±100		mA
T <sub>STG</sub>	Storage Temperature		-65 to +150		°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

## **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter		Min	Max	Unit
$V_{CCA}, V_{CCB}$	Positive DC Supply Voltage		0.9	4.5	V
VI	Bus Input Voltage		GND	4.5	V
V <sub>C</sub>	Control Input	ŌĒ	GND	4.5	V
V <sub>IO</sub>	Bus Output Voltage (Power Down Mode)	Bn	GND	4.5	V
	(Active Mode)	B <sub>n</sub>	GND	V <sub>CCB</sub>	V
	(Tri-State Mode)	B <sub>n</sub>	GND	4.5	V
T <sub>A</sub>	Operating Temperature Range		-40	+85	°C
Δt / ΔV	Input Transition Rise or Rate V <sub>I</sub> , from 30% to 70% of V <sub>CC</sub> ; V <sub>CC</sub> = 3.3 V $\pm$ 0.3 V		0	10	nS

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

#### DC ELECTRICAL CHARACTERISTICS

					–40°C te		
Symbol	Parameter	Test Conditions	V <sub>CCA</sub> (V)	V <sub>CCB</sub> (V)	Min	Max	Unit
V <sub>IH</sub>	Input HIGH Voltage		3.6 – 4.5	0.9 – 4.5	2.2	-	V
	(An, OE)		2.7 – 3.6		2.0	-	
			2.3 – 2.7		1.6	_	
			1.4 – 2.3		0.65 * V <sub>CCA</sub>	_	
			0.9 – 1.4		0.9 * V <sub>CCA</sub>	-	
V <sub>IL</sub>	Input LOW Voltage		3.6 – 4.5	0.9 - 4.5	-	0.8	V
	(An, OE)		2.7 – 3.6		-	0.8	
			2.3 – 2.7		-	0.7	
			1.4 – 2.3		-	0.35 * V <sub>CCA</sub>	
			0.9 – 1.4		-	0.1 * V <sub>CCA</sub>	
V <sub>OH</sub>	Output HIGH Voltage	$I_{OH} = -100 \ \mu\text{A}; \ V_I = V_{IH}$	0.9 – 4.5	0.9 – 4.5	V <sub>CCB</sub> – 0.2	-	V
		$I_{OH} = -0.5 \text{ mA}; V_I = V_{IH}$	0.9	0.9	0.75 * V <sub>CCB</sub>	-	
		$I_{OH} = -2 \text{ mA}; V_I = V_{IH}$	1.4	1.4	1.05	-	
		$I_{OH} = -6 \text{ mA}; V_I = V_{IH}$	1.65	1.65	1.25	-	
			2.3	2.3	2.0	-	
		$I_{OH} = -12 \text{ mA}; V_I = V_{IH}$	2.3	2.3	1.8	-	
			2.7	2.7	2.2	-	
		$I_{OH} = -18 \text{ mA}; V_I = V_{IH}$	2.3	2.3	1.7	-	
			3.0	3.0	2.4	-	
		$I_{OH} = -24 \text{ mA}; V_I = V_{IH}$	3.0	3.0	2.2	-	
V <sub>OL</sub>	Output LOW Voltage	$I_{OL}$ = 100 $\mu$ A; $V_I$ = $V_{IL}$	0.9 – 4.5	0.9 - 4.5	-	0.2	V
		$I_{OL} = 0.5 \text{ mA}; V_I = V_{IL}$	1.1	1.1	-	0.3	
		$I_{OL} = 2 \text{ mA}; V_I = V_{IL}$	1.4	1.4	-	0.35	
		$I_{OL} = 6 \text{ mA}; V_I = V_{IL}$	1.65	1.65	-	0.3	
		$I_{OL} = 12 \text{ mA}; V_I = V_{IL}$	2.3	2.3	-	0.4	
			2.7	2.7	_	0.4	
		$I_{OL}$ = 18 mA; $V_I = V_{IL}$	2.3	2.3	-	0.6	
			3.0	3.0	_	0.4	
		$I_{OL}$ = 24 mA; $V_I$ = $V_{IL}$	3.0	3.0	-	0.55	
l <sub>l</sub>	Input Leakage Current	$V_I = V_{CCA}$ or GND	0.9 – 4.5	0.9 – 4.5	-1.0	1.0	μA
I <sub>OFF</sub>	Power-Off Leakage Current	<u>OE</u> = 0 V	0 0.9 – 4.5	0.9 – 4.5 0	-1.0 -1.0	1.0 1.0	μA
I <sub>CCA</sub>	Quiescent Supply Current		0.9 – 4.5	0.9 – 4.5	-	1.0	μA
I <sub>CCB</sub>	Quiescent Supply Current		0.9 – 4.5	0.9 – 4.5	-	1.0	μA
<sub>CCA</sub> + I <sub>CCB</sub>	Quiescent Supply Current		0.9 – 4.5	0.9 – 4.5	-	2.0	μΑ
$\Delta I_{CCA}$	Increase in $I_{CC}$ per Input Voltage, Other Inputs at $V_{CCA}$ or GND	$V_{I} = V_{CCA} - 0.6 V;$ $V_{I} = V_{CCA} \text{ or GND}$	4.5 3.6	4.5 3.6	-	10 5.0	μA
$\Delta I_{CCB}$	Increase in $I_{CC}$ per Input Voltage, Other Inputs at $V_{CCA}$ or GND	$V_{I} = V_{CCA} - 0.6 V;$ $V_{I} = V_{CCA}$ or GND	4.5 3.6	4.5 3.6	-	10 5.0	μA
I <sub>OZ</sub>	I/O Tri-State Output Leakage	$T_A = 25^{\circ}C, \overline{OE} = 0 V$	0.9 – 4.5	0.9 – 4.5	-1.0	1.0	μA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

### TOTAL STATIC POWER CONSUMPTION (I<sub>CCA</sub> + I<sub>CCB</sub>)

					–40°C t	o +85°C					
					Vcc	<sub>в</sub> (V)					
	4	.5	3	.3	2	.8	1	.8	0	.9	
V <sub>CCA</sub> (V)	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Unit
4.5		2		2		2		2		< 1.5	μΑ
3.3		2		2		2		2		< 1.5	μΑ
2.8		< 2		< 1		< 1		< 0.5		< 0.5	μΑ
1.8		< 1		< 1		< 0.5		< 0.5		< 0.5	μΑ
0.9		< 0.5		< 0.5		< 0.5		< 0.5		< 0.5	μA

NOTE: Connect ground before applying supply voltage V<sub>CCA</sub> or V<sub>CCB</sub>. This device is designed with the feature that the power–up sequence of V<sub>CCA</sub> and V<sub>CCB</sub> will not damage the IC.

#### **AC ELECTRICAL CHARACTERISTICS**

							–40°C t	o +85°C					
			V <sub>CCB</sub> (V)										
			4	.5	3	.3	2	.8	1	.8	1	.2	
Symbol	Parameter	V <sub>CCA</sub> (V)	Min	Max	Min	Мах	Min	Max	Min	Мах	Min	Max	Unit
t <sub>PLH</sub> ,	Propagation	4.5		1.6		1.8		2.0		2.1		2.3	nS
t <sub>PHL</sub> (Note 1)	Delay,	3.3		1.7		1.9		2.1		2.3		2.6	
(Note I)	A <sub>n</sub> to B <sub>n</sub>	2.8		1.9		2.1		2.3		2.5		2.8	
		1.8		2.1		2.4		2.5		2.7		3.0	
		1.2		2.4		2.7		2.8		3.0		3.3	
t <sub>PZH</sub> ,	Output	4.5		2.6		3.8		4.0		4.1		4.3	nS
t <sub>PZL</sub> (Note 1)	Enable,	3.3		3.7		3.9		4.1		4.3		4.6	
(NOLE T)	OE to B <sub>n</sub>	2.5		3.9		4.1		4.3		4.5		4.8	1
		1.8		4.1		4.4		4.5		4.7		5.0	
		1.2		4.4		4.7		4.8		5.0		5.3	
t <sub>PHZ</sub> ,	Output	4.5		2.6		3.8		4.0		4.1		4.3	nS
t <sub>PLZ</sub> (Note 1)	Disable,	3.3		3.7		3.9		4.1		4.3		4.6	
(Note T)	OE to B <sub>n</sub>	2.5		3.9		4.1		4.3		4.5		4.8	
		1.8		4.1		4.4		4.5		4.7		5.0	
		1.2		4.4		4.7		4.8		5.0		5.3	
t <sub>OSHL</sub> ,	Output to	4.5		0.15		0.15		0.15		0.15		0.15	nS
t <sub>OSLH</sub> (Note 1)	Output Skew,	3.3		0.15		0.15		0.15		0.15		0.15	1
	Time	2.5		0.15		0.15		0.15		0.15		0.15	
		1.8		0.15		0.15		0.15		0.15		0.15	
		1.2		0.15		0.15		0.15		0.15		0.15	

1. Propagation delays defined per Figure 2.

CAPACITANCE

Symbol	Parameter	Test Conditions	Typ (Note 2)	Unit
C <sub>IN</sub>	Control Pin Input Capacitance	$V_{CCA} = V_{CCB} = 3.3 \text{ V}, V_I = 0 \text{ V or } V_{CCA/B}$	3.5	pF
C <sub>I/O</sub>	I/O Pin Input Capacitance	$V_{CCA}$ = $V_{CCB}$ = 3.3 V, $V_{I}$ = 0 V or $V_{CCA/B}$	5.0	pF
C <sub>PD</sub>	Power Dissipation Capacitance	$V_{CCA}$ = $V_{CCB}$ = 3.3 V, $V_{I}$ = 0 V or $V_{CCA},f$ = 10 MHz	20	pF

2. Typical values are at  $T_A = +25^{\circ}C$ . 3.  $C_{PD}$  is defined as the value of the IC's equivalent capacitance from which the operating current can be calculated from:  $I_{CC(operating)} \cong C_{PD} \times V_{CC} \times f_{IN} \times N_{SW}$  where  $I_{CC} = I_{CCA} + I_{CCB}$  and  $N_{SW}$  = total number of outputs switching.

# NLSV2T244

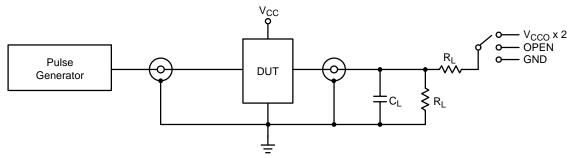
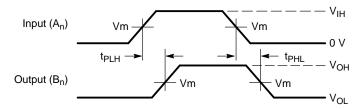
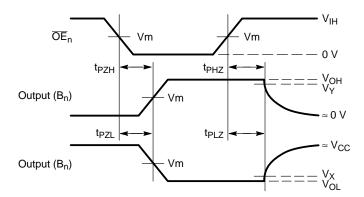


Figure 2. AC (Propagation Delay) Test Circuit

Test	Switch
t <sub>PLH</sub> , t <sub>PHL</sub>	OPEN
t <sub>PLZ</sub> , t <sub>PZL</sub>	V <sub>CCO</sub> x 2
t <sub>PHZ</sub> , t <sub>PZH</sub>	GND
$C_L$ = 15 pF or equivalent (include $R_L$ = 2 k $\Omega$ or equivalent $Z_{OUT}$ of pulse generator = 50 $\Omega$	es probe and jig capacitance)



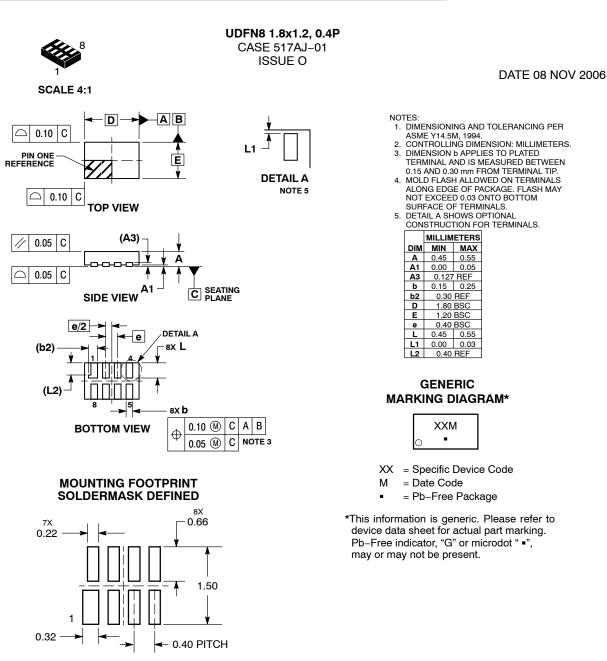
 $\label{eq:waveform 1 - Propagation Delays} \begin{matrix} t_{R} = t_{F} = 2.0 \text{ ns}, 10\% \text{ to } 90\%; f = 1 \text{ MHz}; t_{W} = 500 \text{ ns} \end{matrix}$ 



Waveform 2 – Output Enable and Disable Times  $t_R$  =  $t_F$  = 2.0 ns, 10% to 90%; f = 1 MHz;  $t_W$  = 500 ns

		V <sub>CC</sub>									
Symbol	3.0 V – 4.5 V	2.3 V – 2.7 V	1.65 V – 1.95 V	1.4 V – 1.6 V	0.9 V – 1.3 V						
V <sub>mA</sub>	V <sub>CCA</sub> /2										
V <sub>mB</sub>	V <sub>CCB</sub> /2										
V <sub>X</sub>	V <sub>OL</sub> x 0.1										
V <sub>Y</sub>	V <sub>OH</sub> x 0.9										





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\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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#### SOIC-8 NB CASE 751-07 ISSUE AK

STYLE 1: PIN 1. EMITTER COLLECTOR 2. COLLECTOR 3. 4. EMITTER 5. EMITTER BASE 6. 7 BASE EMITTER 8. STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN DRAIN 4. GATE 5. 6. GATE SOURCE 7. 8. SOURCE STYLE 9: PIN 1. EMITTER, COMMON COLLECTOR, DIE #1 COLLECTOR, DIE #2 2. З. EMITTER, COMMON 4. 5. EMITTER, COMMON 6 BASE. DIE #2 BASE, DIE #1 7. 8. EMITTER, COMMON STYLE 13: PIN 1. N.C. 2. SOURCE 3 GATE 4. 5. DRAIN 6. DRAIN DRAIN 7. DRAIN 8. STYLE 17: PIN 1. VCC 2. V2OUT V10UT З. TXE 4. 5. RXE 6. VFF 7. GND 8. ACC STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3 CATHODE 3 CATHODE 4 4. 5. CATHODE 5 6. COMMON ANODE COMMON ANODE 7. 8. CATHODE 6 STYLE 25: PIN 1. VIN 2 N/C REXT З. 4. GND 5. IOUT 6. IOUT IOUT 7. 8. IOUT STYLE 29: BASE, DIE #1 PIN 1. 2 EMITTER, #1 BASE, #2 З. EMITTER, #2 4. 5 COLLECTOR, #2

STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 COLLECTOR, #2 3. 4 COLLECTOR, #2 BASE, #2 5. EMITTER, #2 6. 7 BASE #1 EMITTER, #1 8. STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN SOURCE 4. SOURCE 5. 6. GATE GATE 7. 8. SOURCE STYLE 10: GROUND PIN 1. BIAS 1 OUTPUT 2. З. GROUND 4. 5. GROUND 6 BIAS 2 INPUT 7. 8. GROUND STYLE 14: PIN 1. N-SOURCE 2. N-GATE P-SOURCE 3 P-GATE 4. P-DRAIN 5 6. P-DRAIN N-DRAIN 7. N-DRAIN 8. STYLE 18: PIN 1. ANODE 2. ANODE SOURCE 3. GATE 4. 5. DRAIN 6 DRAIN CATHODE 7. CATHODE 8. STYLE 22 PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3 COMMON CATHODE/VCC 4. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND STYLE 26: PIN 1. GND 2 dv/dt З. ENABLE 4. ILIMIT 5. SOURCE SOURCE 6. SOURCE 7. 8. VCC STYLE 30: DRAIN 1 PIN 1. DRAIN 1 2 GATE 2 З. SOURCE 2 4. SOURCE 1/DRAIN 2 SOURCE 1/DRAIN 2 5. 6.

STYLE 3: PIN 1. DRAIN, DIE #1 DRAIN, #1 2. DRAIN, #2 З. 4. DRAIN, #2 GATE, #2 5. SOURCE, #2 6. 7 GATE #1 8. SOURCE, #1 STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS THIRD STAGE SOURCE GROUND З. 4. 5. DRAIN 6. GATE 3 SECOND STAGE Vd 7. FIRST STAGE Vd 8. STYLE 11: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. 3. GATE 2 4. 5. DRAIN 2 6. DRAIN 2 DRAIN 1 7. 8. DRAIN 1 STYLE 15: PIN 1. ANODE 1 2. ANODE 1 ANODE 1 3 ANODE 1 4. 5. CATHODE, COMMON CATHODE, COMMON CATHODE, COMMON 6. 7. CATHODE, COMMON 8. STYLE 19: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. 3. GATE 2 4. 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. **MIRROR 1** STYLE 23: PIN 1. LINE 1 IN COMMON ANODE/GND COMMON ANODE/GND 2. 3 LINE 2 IN 4. LINE 2 OUT 5. COMMON ANODE/GND COMMON ANODE/GND 6. 7. LINE 1 OUT 8. STYLE 27: PIN 1. ILIMIT 2 OVI 0 UVLO З. 4. INPUT+ 5. SOURCE SOURCE 6. SOURCE 7. 8 DRAIN

#### DATE 16 FEB 2011

STYLE 4: PIN 1. 2. ANODE ANODE ANODE З. 4. ANODE ANODE 5. 6. ANODE 7 ANODE COMMON CATHODE 8. STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 BASE, #2 З. COLLECTOR, #2 4. COLLECTOR, #2 5. 6. EMITTER, #2 EMITTER, #1 7. 8. COLLECTOR, #1 STYLE 12: PIN 1. SOURCE SOURCE 2. 3. GATE 4. 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 EMITTER, DIE #2 3 BASE, DIE #2 4. 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 COLLECTOR, DIE #1 7. COLLECTOR, DIE #1 8. STYLE 20: PIN 1. SOURCE (N) GATE (N) SOURCE (P) 2. 3. 4. GATE (P) 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 24: PIN 1. BASE 2. EMITTER 3 COLLECTOR/ANODE COLLECTOR/ANODE 4. 5. CATHODE 6. CATHODE COLLECTOR/ANODE 7. 8. COLLECTOR/ANODE STYLE 28: PIN 1. SW\_TO\_GND 2. DASIC OFF DASIC\_SW\_DET З. 4. GND 5. 6. V MON VBULK 7. VBULK 8 VIN

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